

SMALL SIGNAL SCHOTTKY DIODE

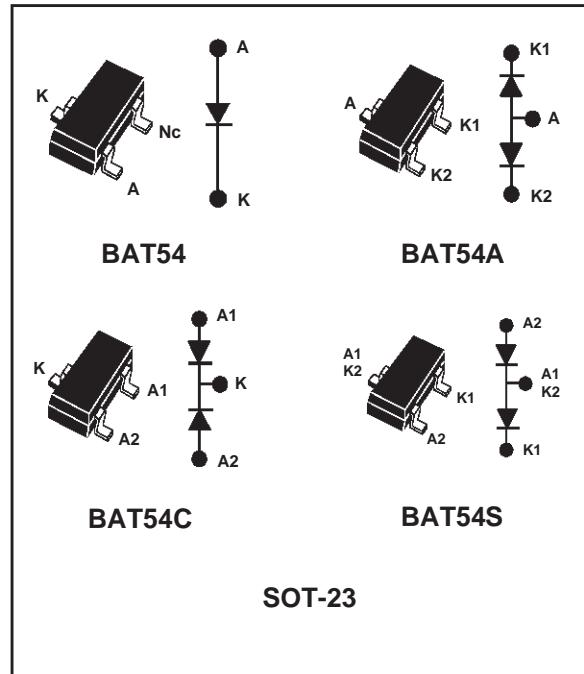
FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD VOLTAGE DROP
- SURFACE MOUNT DEVICE

DESCRIPTION

Schottky barrier diodes encapsulated in a SOT-23 small SMD packages.

Single and double diodes with different pinning are available.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	30	V
I_F	Continuous forward current	0.3	A
I_{FSM}	Surge non repetitive forward current tp=10ms sinusoidal	1	A
P_{tot}	Power dissipation (note 1)	250	mW
T_{stg}	Maximum storage temperature range	- 65 to +150	°C
T_j	Maximum operating junction temperature *	150	°C
T_L	Maximum temperature for soldering during 10s	260	°C

Note 1: for double diodes, P_{tot} is the total dissipation of both diodes

$$* : \frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)} \text{ thermal runaway condition for a diode on its own heatsink}$$

BAT54 series

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Junction to ambient (*)	400	°C/W

(*) Mounted on ceramic substrate: 7 x 5 x 0.5 mm

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameters	Tests Conditions	Min.	Typ.	Max.	Unit
V_F *	Forward voltage drop	$T_{amb} = 25^\circ C$	$I_F = 0.1$ mA		240	mV
			$I_F = 1$ mA		320	
			$I_F = 10$ mA		400	
			$I_F = 30$ mA		500	
			$I_F = 100$ mA		900	
I_R **	Reverse current	$T_{amb} = 25^\circ C$	$V_R = 30$ V		1	μA
		$T_{amb} = 100^\circ C$			100	

Pulse test : * $t_p = 380 \mu s, \delta < 2\%$

** $t_p = 5 ms, \delta < 2\%$

DYNAMIC CHARACTERISTICS ($T_j = 25^\circ C$)

Symbol	Parameters	Tests Conditions	Min.	Typ.	Max.	Unit
C	Junction Capacitance	$T_{amb} = 25^\circ C \quad V_R = 1 V \quad f = 1 MHz$			10	pF
t_{rr}	Reverse Recovery Time	$I_F = 10$ mA $I_{rr} = 10$ mA $I_{rr} = 1$ mA $R_L = 100 \Omega$			5	ns

Fig.1 : Average forward power dissipation versus average forward current.

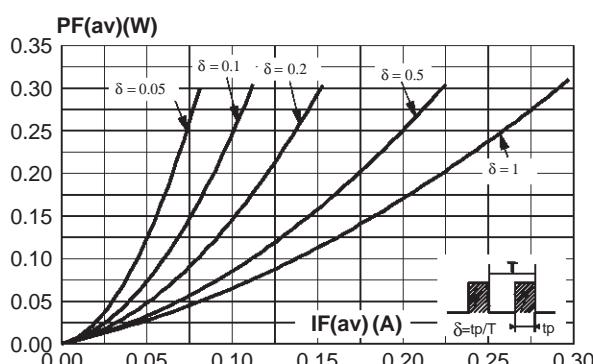


Fig.2 : Average forward current versus ambient temperature ($\delta = 1$).

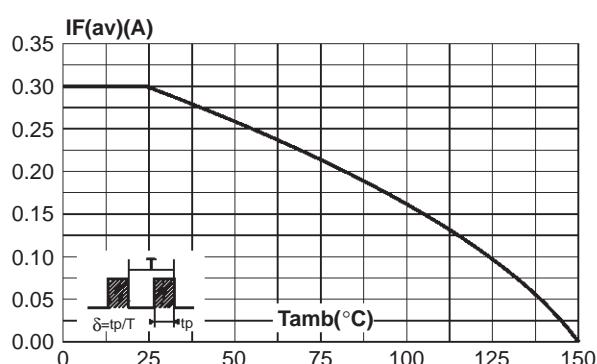


Fig.3 : Non repetitive surge peak forward current versus overload duration (maximum values).

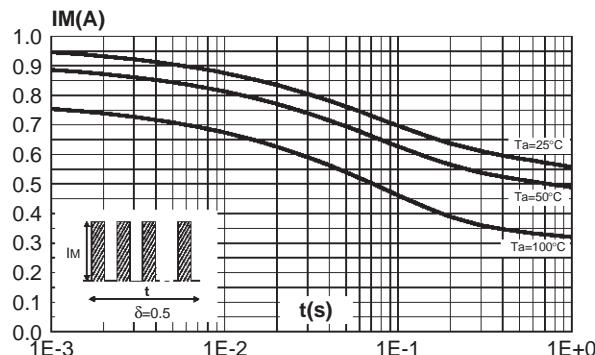


Fig.5 : Reverse leakage current versus reverse voltage applied (typical values).

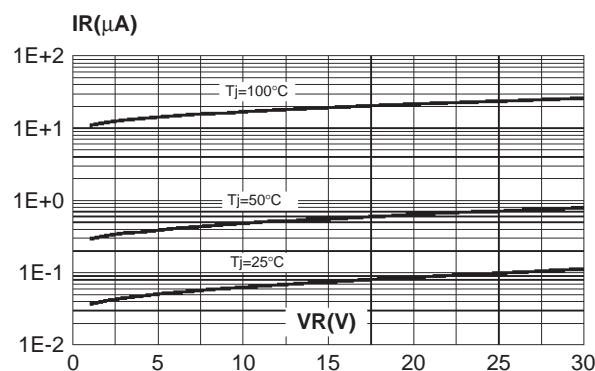


Fig.7 : Junction capacitance versus reverse voltage applied (typical values).

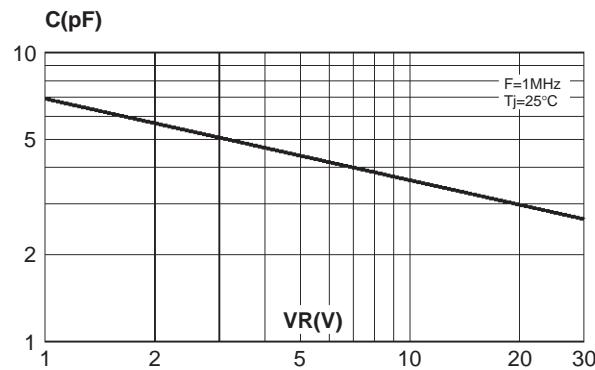


Fig.4 : Relative variation of thermal impedance junction to ambient versus pulse duration (alumine substrate 10mm x 8mm x 0.5mm).

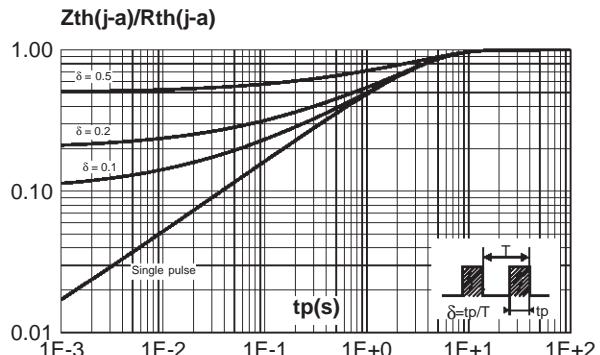


Fig.6 : Reverse leakage current versus junction temperature.

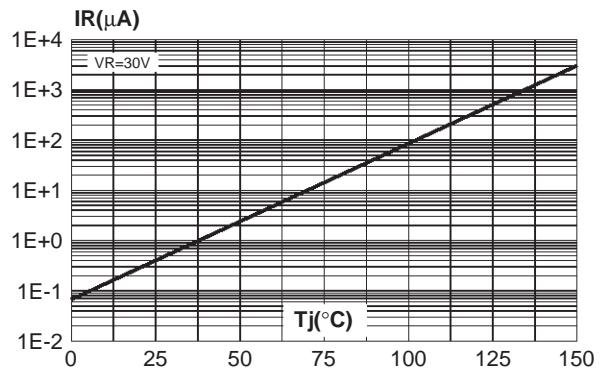
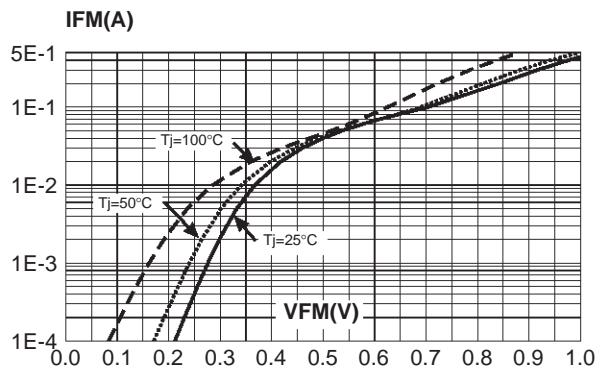


Fig.8 : Forward voltage drop versus forward current (typical values).



BAT54 series

PACKAGE MECHANICAL DATA SOT-23

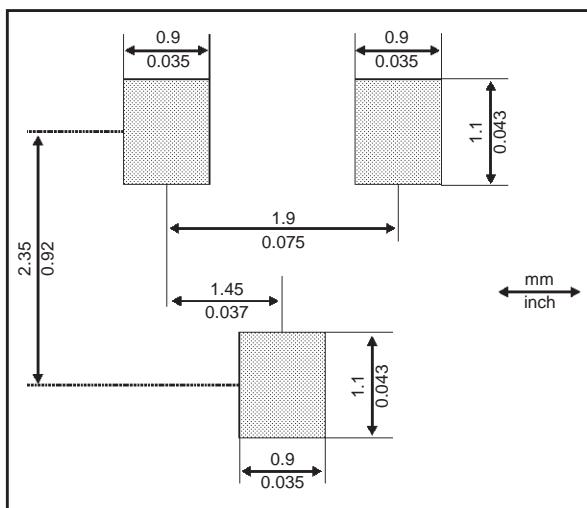
REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.64	1.3	0.025	0.051
A1	0	0.1	0	0.004
B	0.3	0.54	0.012	0.021
c	0.085	0.18	0.003	0.007
D	2.67	3.05	0.105	0.120
e	0.89	1.05	0.035	0.041
e1	1.7	2.1	0.067	0.083
E	1.2	1.6	0.047	0.063
H	2.1	2.75	0.083	0.108
S	0.35	0.65	0.014	0.026

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
BAT54FILM	D86	SOT-23	0.01g	3000	Tape & reel
BAT54AFILM	D84	SOT-23	0.01g	3000	Tape & reel
BAT54CFILM	D87	SOT-23	0.01g	3000	Tape & reel
BAT54SFILM	D88	SOT-23	0.01g	3000	Tape & reel

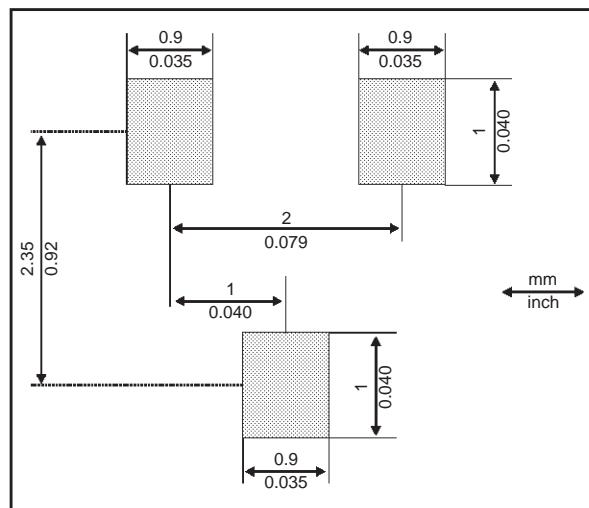
■ Epoxy meets UL94,V0

FOOTPRINT DIMENSIONS

COMPATIBLE SOT-23 / SC-59
(in millimeters and inches)

**OPTIMIZED SOT-23 FOOTPRINT DIMENSIONS**

(in millimeters and inches)



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